

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5550

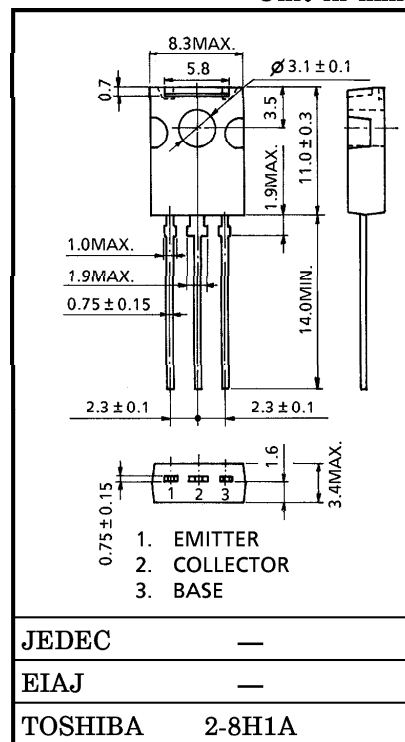
HIGH SPEED SWITCHING APPLICATION FOR INVERTER LIGHTING SYSTEM

Unit in mm

- Suitable for R_{CC} Circuit. (Guaranteed small current h_{FE})
: $h_{FE}=13$ (Min.) ($I_C=1mA$)
- High Speed : $t_r=0.5\mu s$ (Max.), $t_f=0.3\mu s$ (Max.) ($I_C=0.24A$)
- High Voltage : $V_{CEO}=400V$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	DC	I_C	1
	Pulse	I_{CP}	2
Base Current	I_B	0.5	A
Collector Power Dissipation	$T_a=25^\circ C$	P_C	1.5
	$T_c=25^\circ C$		10
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 0.82g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 320V, I _E = 0	—	—	100	μA
Emitter Cut-off Current		IEBO	VEB = 7V, IC = 0	—	—	100	μA
Collector-Base Breakdown Voltage		V _{(BR)CBO}	IC = 1mA, IB = 0	400	—	—	V
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	IC = 10mA, IB = 0	400	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 5V, IC = 1mA	13	—	—	
		h _{FE} (2)	V _{CE} = 5V, IC = 0.04A	20	—	65	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	IC = 0.2A, IB = 25mA	—	—	1.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}	IC = 0.2A, IB = 25mA	—	—	1.3	V
Switching Time	Rise Time	t _r	<p>20μs V_{CC} = 200V IB1 IB2 IC INPUT OUTPUT 833Ω</p>	—	—	0.5	μs
	Storage Time	t _{stg}		—	—	5.0	
	Fall Time	t _f		IB1 = 0.03A, IB2 = -0.06A DUTY CYCLE ≤ 1%	—	—	

